PCN Number:	2023112	29001	. 1			PC	N D	ate:	Nove	mber 30, 2023	
Title: Qualification	of LFAB a	nd RF	AB as ad	ditiona	l optior	ns fo	r M	ETDCU	proces	ssing	
Customer Contact:	Change Ma	anage	ment tea	am	Dept:		Qua	lity Se	ervices		
Proposed 1 st Ship Date							ple requests epted until: Dec 30, 2023*				
*Sample requests rece	ived afte	r De	cember	29, 20	23 wil	l no	t be	supp	orted.		
Change Type:											
Assembly Site			Design							Material	
Assembly Process		141	Data Sh							Process	
Assembly Materials		141	Part nur		hange				r Fab S		
Mechanical Specifica		$+$ \vdash \mid	Test Sit				<u> </u>		r Fab M		
☐ Packing/Shipping/Lal	beling		Test Pro		<u> </u>		Ш	Wafe	r Fab P	rocess	
	PCN Details										
Description of Change:				li.C.				LDEAR	<u> </u>	100	
Texas Instruments is plea											
for METDCU processing for	or the sele	ecteu	uevices i	iistea t	elow III	the	pro	uuct a	mecteu	Section.	
Current I	ab Site					Add	itio	nal Fa	b Site		
Current Fab Pro	cess	Wafer Additional				P	rocess	5	Wafer		
Site		Dia	meter	Fab	Site					Diameter	
DMOS6 LE	C9	30	0 mm	L	AB			LBC9		300 mm	
DM030 LE		50	O IIIIII	RI	RFAB LB0			LBC9		300 mm	
Qual details are provided	in the Qu	al Da	ta Sectio	n.							
Reason for Change:											
Capacity increase to supp	ort dema	nd an	d continu	uity of	supply						
Anticipated impact on	Fit, Form	, Fun	ction, Q	ua lity	or Rel	ia bi	lity	(posi	tive /	negative):	
No anticipated impact.											
· · · · · · · · · · · · · · · · · · ·	anticipated impact.										
Changes to product ide	ntification	on re	sulting f	rom t	his PCI	N:					
Changes to product ide	ntification	on re	sulting f	from t	his PCI	N:					
	ntification	on re:	sulting f	from t	his PCI	N:					
None	entification				his PCI		Q1				

Qualification Results

Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name	Condition	Duration	Qual Device: BQ79616HPAPRQ1	QBS Reference: BQ79616PAPRQ1
Test Group	A - Acce	lerated Environment Stre	ess Tests	•					
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	3/231/0	-
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	3/231/0	-
тс	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	-
PTC	A5	JEDEC JESD22-A105	1	45	PTC	-40/125C	1000 Cycles	-	1/45/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	175C	500 Hours	3/135/0	-
Test Group	B - Acce	lerated Lifetime Simulation	on Tests						
HTOL	B1	JEDEC JESD22-A108	1	77	Life Test	125C	1000 Hours	3/231/0	-
ELFR	B2	AEC Q100-008	1	77	Early Life Failure Rate	125C	48 Hours	3/2400/0	-
Test Group	C - Pack	age Assembly Integrity T	ests						
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	-
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	-
SD	C3	JEDEC JESD22-B102	1	15	PB Solderability	>95% Lead Coverage	-	1/15/0	-
SD	C3	JEDEC JESD22-B102	1	15	PB-Free Solderability	>95% Lead Coverage	-	1/15/0	-
Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: <u>BQ79616HPAPRQ1</u>	QBS Reference: BQ79616PAPRQ1
Type	# C4	Test Spec JEDEC JESD22-B100 and B108	Lot		Test Name Physical Dimensions	Condition Cpk>1.67	Duration		
PD	C4	JEDEC JESD22-B100	Lot Qty	Lot	Physical		Duration -	BQ79616HPAPRQ1	
PD	C4	JEDEC JESD22-B100 and B108	Lot Qty	Lot	Physical		Duration -	BQ79616HPAPRQ1	
PD Test Group	C4 D - Die F	JEDEC JESD22-B100 and B108 Fabrication Reliability Tes	Lot Qty	Lot 10	Physical Dimensions	Cpk>1.67	Duration - -	BQ79616HPAPRQ1 3/30/0 Completed Per Process Technology	BQ79616PAPRQ1 - Completed Per Process Technology
PD Test Group	C4 D - Die F	JEDEC JESD22-B100 and B108 Fabrication Reliability Tes JESD61	Lot Qty 1 ts	10 -	Physical Dimensions Electromigration Time Dependent Dielectric	Cpl⇔1.67	Duration -	BQ79616HPAPRQ1 3/30/0 Completed Per Process Technology Requirements Completed Per Process Technology	EQ79616PAPRQ1 - Completed Per Process Technology Requirements Completed Per Process Technology
PD Test Group EM TDDB	C4 D - Die F D1 D2	JEDEC JESD22-B100 and B108 Fabrication Reliability Tes JESD61	Lot Qty 1 ts	10	Physical Dimensions Electromigration Time Dependent Dielectric Breakdown Hot Carrier	Cpl⇔1.67	Duration -	BQ79616HPAPRQ1 3/30/0 Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology Requirements
PD Test Group EM TDDB	C4 D - Die F D1 D2 D3	JEDEC JESD22-B100 and B108 -abrication Reliability Tes JESD61 JESD35 JESD60 & 28	Lot Qty 1 ts	10	Physical Dimensions Electromigration Time Dependent Dielectric Breakdown Hot Carrier Injection Negative Bias Temperature	Cpk>1.67	Duration	BQ79616HPAPRQ1 3/30/0 Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology
PD Test Group EM TDDB HCI NBTI SM	D - Die F D1 D2 D3 D4 D5	JEDEC JESD22-B100 and B108 -abrication Reliability Tes JESD61 JESD35 JESD60 & 28	Lot Qty 1 ts -		Physical Dimensions Electromigration Time Dependent Dielectric Breakdown Hot Carrier Injection Negative Bias Temperature Instability	Cpk>1.67	Duration	BQ79616HPAPRQ1 3/30/0 Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
PD Test Group EM TDDB HCI NBTI SM	D - Die F D1 D2 D3 D4 D5	JEDEC JESD22-B100 and B108 Fabrication Reliability Tes JESD61 JESD35 JESD60 & 28	Lot Qty 1 ts -		Physical Dimensions Electromigration Time Dependent Dielectric Breakdown Hot Carrier Injection Negative Bias Temperature Instability	Cpk>1.67	Duration 3000 Volts	BQ79616HPAPRQ1 3/30/0 Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
PD Test Group EM TDDB HCI NBTI SM Test Group	D - Die F D1 D2 D3 D4 D5 E - Elect	JEDEC JESD22-B100 and B108 Fabrication Reliability Tes JESD61 JESD35 JESD60 & 28 - - trical Verification Tests	Lot Qty 1 ts -		Physical Dimensions Electromigration Time Dependent Dielectric Breakdown Hot Carrier Injection Negative Bias Temperature Instability Stress Migration	Cpl>1.67		BQ79616HPAPRQ1 3/30/0 Completed Per Process Technology Requirements Requirements	Completed Per Process Technology Requirements
PD Test Group EM TDDB HCI NBTI SM Test Group ESD	D - Die F D1 D2 D3 D4 D5 E - Elect E2	JEDEC JESD22-B100 and B108 Fabrication Reliability Tes JESD61 JESD35 JESD60 & 28 - - trical Verification Tests AEC Q100-002	Lot Qty 1 ts 1	3	Physical Dimensions Electromigration Time Dependent Dielectric Breakdown Hot Carrier Injection Negative Bias Temperature Instability Stress Migration	Cpk>1.67		BQ79616HPAPRQ1 3/30/0 Completed Per Process Technology Requirements 1/3/0	Completed Per Process Technology Requirements
PD Test Group EM TDDB HCI NBTI SM Test Group ESD ESD	D - Die F D1 D2 D3 D4 D5 E - Elect E2 E3	JEDEC JESD22-B100 and B108 Fabrication Reliability Tes JESD61 JESD35 JESD60 & 28 trical Verification Tests AEC Q100-002 AEC Q100-011	Lot Qty 1 ts 1 1	3 3 3	Physical Dimensions Electromigration Time Dependent Dielectric Breakdown Hot Carrier Injection Negative Bias Temperature Instability Stress Migration ESD HBM ESD CDM			BQ79616HPAPRQ1 3/30/0 Completed Per Process Technology Requirements Lompleted Per Process Technology Requirements Technology Requirements 1/3/0	Completed Per Process Technology Requirements -

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

- QBS: Qual By Similarity
- Qual Device BQ79616HPAPRQ1 is qualified at MSL3 260C
- The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-NPD-2202-003

Automotive New Product Qualification Summary (As per AEC-Q100, AEC-Q006, and JEDEC Guidelines)

Qualification Results

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: <u>BQ79616HPAPRQ1</u>
Test G	oup A - A	Accelerated Environment Str	ess Tests					
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL3 260C	1 Step	No Fails
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	1 Step	3/66/0
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	1 Step	3/66/0
HAST	A2.1	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	3/231/0
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	3/3/0
HAST	A2.1.3	-	3	30	Wire Bond Shear, post bHAST, 1X	Post stress	Wires	3/9/0
HAST	A2.1.4	-	3	30	Bond Pull over Stitch, post bHAST, 1X	Post stress	Wires	3/9/0

Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name	Condition	Duration	Qual Device: <u>BQ79616HPAPRQ1</u>
HAST	A2.1.5	-	3	30	Bond Pull over Ball, post bHAST, 1X	Post stress	Wires	3/9/0
HAST	A2.2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	192 Hours	3/210/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	3/66/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	3/3/0
HAST	A2.2.3	-	3	30	Wire Bond Shear, post bHAST, 2X	Post stress	Wires	3/9/0
HAST	A2.2.4	-	3	30	Bond Pull over Stitch, post bHAST, 2X	Post stress	Wires	3/9/0
HAST	A2.2.5	-	3	30	Bond Pull over Ball, post bHAST, 2X	Post stress	Wires	3/9/0
TC	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0
TC	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	3/66/0
TC	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	3/3/0
TC	A4.1.3	-	3	30	Wire Bond Shear, post TC, 1X	Post stress	Wires	3/9/0
TC	A4.1.4	-	3	30	Bond Pull over Stitch, post TC, 1X	Post stress	Wires	3/9/0
TC	A4.1.5	-	3	30	Bond Pull over Ball, post TC, 1X	Post stress	Wires	3/9/0
TC	A4.2	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	1000 Cycles	3/210/0
TC	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	3/66/0
TC	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	3/3/0
TC	A4.2.3	-	3	30	Wire Bond Shear, post TC, 2X	Post stress	Wires	3/9/0
TC	A4.2.4	-	3	30	Bond Pull over Stitch, post TC, 2X	Post stress	Wires	3/9/0

Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name	Condition	Duration	Qual Device: <u>BQ79616HPAPRQ1</u>
TC	A4.2.5	-	3	30	Bond Pull over Ball, post TC, 2X	Post stress	Wires	3/9/0
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	175C	500 Hours	3/135/0
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	3/3/0
HTSL	A6.2	JEDEC JESD22-A103	3	45	High Temperature Storage Life	175C	1000 Hours	3/132/0
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	3/3/0
Test Gr	roup B - A	Accelerated Lifetime Simulat	ion Tests					
HTOL	B1	JEDEC JESD22-A108	1	77	Life Test	125C	1000 Hours	3/231/0
ELFR	B2	AEC Q100-008	1	77	Early Life Failure Rate	125C	48 Hours	3/2400/0
Test Gr	roup C - F	Package Assembly Integrity	Tests					
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0
SD	C3	JEDEC JESD22-B102	1	15	PB Solderability	>95% Lead Coverage	-	1/15/0
SD	C3	JEDEC JESD22-B102	1	15	PB-Free Solderability	>95% Lead Coverage	-	1/15/0
PD	C4	JEDEC JESD22-B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	3/30/0
Test Gr	roup D - E	Die Fabrication Reliability Tes	sts					
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	_	_	Hot Carrier Injection	_	_	Completed Per Process

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: BQ79616HPAPRQ1
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements
Test G	roup E - E	Electrical Verification Tests						
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	3000 Volts	1/3/0
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	1000 Volts	1/3/0
LU	E4	AEC Q100-004	1	6	Latch-Up	Per AEC Q100-004	-	1/6/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	3/90/0

- · Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-NPD-2202-003

Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

Qualification Results

Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name	Condition	Duration	Qual Device: BQ79616HPAPRQ1	QBS Reference: BQ79616PAPRQ1		
Test Group	Test Group A - Accelerated Environment Stress Tests										
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	3/231/0	-		
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	3/231/0	-		
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	-		
PTC	A5	JEDEC JESD22-A105	1	45	PTC	-40/125C	1000 Cycles	-	1/45/0		
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	175C	500 Hours	3/135/0	-		
Test Group I	B - Acce	elerated Lifetime Simulation	on Tests								
HTOL	B1	JEDEC JESD22-A108	1	77	Life Test	125C	1000 Hours	3/231/1 ¹	-		
ELFR	B2	AEC Q100-008	1	77	Early Life Failure Rate	125C	48 Hours	3/2400/0	-		

Test Group	C - Pack		ests						
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	-
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	-
SD	C3	JEDEC JESD22-B102	1	15	PB Solderability	>95% Lead Coverage	-	-	1/15/0
SD	C3	JEDEC JESD22-B102	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	1/15/0
Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name	Condition	Duration	Qual Device: BQ79616HPAPRQ1	QBS Reference: BQ79616PAPRQ1
PD	C4	JEDEC JESD22-B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	3/30/0	-
Test Group	D - Die F	Fabrication Reliability Tes	ts						
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group	E - Elect	trical Verification Tests							
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2500 Volts	1/3/0	-
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	1000 Volts	1/3/0	-
LU	E4	AEC Q100-004	1	6	Latch-Up	Per AEC Q100-004	-	1/6/0	-
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	3/90/0	-
Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device	QBS Reference

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- $\bullet \quad \text{The following are equivalent HTSL options based on an activation energy of 0.7eV: } 150\text{C/1k Hours, and } 170\text{C/420 Hours} \\$
- QBS: Qual By Similarity
- Qual Device BQ79616HPAPRQ1 is qualified at MSL3 260C
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-NPD-2201-085

[1]-QEM-EVAL-2206-00212: EOS undetermined root cause. Contact QRE for 8D.

Automotive New Product Qualification Summary (As per AEC-Q100, AEC-Q006, and JEDEC Guidelines)

Qualification Results

Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name	Condition	Duration	Qual Device: <u>BQ79616HPAPRQ1</u>	QBS Reference: <u>BQ79616PAPRQ1</u>
Test G	roup A - /	Accelerated Environme	ent Stres	s Tests					
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL3 260C	1 Step	No Fails	-
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	1 Step	3/66/0	-
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	1 Step	3/66/0	-
HAST	A2.1	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	3/231/0	-
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	3/3/0	-
Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: BQ79616HPAPRQ1	QBS Reference: BQ79616PAPRQ1
HAST	A2.1.3	-	3	30	Wire Bond Shear, post bHAST, 1X	Post stress	Wires	3/9/0	-
HAST	A2.1.4	-	3	30	Bond Pull over Stitch, post bHAST, 1X	Post stress	Wires	3/9/0	-
HAST	A2.1.5	-	3	30	Bond Pull over Ball, post bHAST, 1X	Post stress	Wires	3/9/0	-
HAST	A2.2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	192 Hours	3/210/0	-
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	3/66/0	-
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	3/3/0	-
HAST	A2.2.3	-	3	30	Wire Bond Shear, post bHAST, 2X	Post stress	Wires	3/9/0	-
HAST	A2.2.4	-	3	30	Bond Pull over Stitch, post bHAST, 2X	Post stress	Wires	3/9/0	-
HAST	A2.2.5	-	3	30	Bond Pull over Ball, post bHAST, 2X	Post stress	Wires	3/9/0	-
TC	A4.1	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	-
TC	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	3/66/0	-
TC	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	3/3/0	-
TC	A4.1.3	-	3	30	Wire Bond Shear, post TC, 1X	Post stress	Wires	3/9/0	-
TC	A4.1.4	-	3	30	Bond Pull over Stitch, post TC, 1X	Post stress	Wires	3/9/0	-
тс	A4.1.5	-	3	30	Bond Pull over Ball, post TC, 1X	Post stress	Wires	3/9/0	-

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: BQ79616HPAPRQ1	QBS Reference: BQ79616PAPRQ1
тс	A4.2	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	1000 Cycles	3/210/0	-
TC	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	3/66/0	-
TC	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	3/3/0	-
TC	A4.2.3	-	3	30	Wire Bond Shear, post TC, 2X	Post stress	Wires	3/9/0	-
TC	A4.2.4	-	3	30	Bond Pull over Stitch, post TC, 2X	Post stress	Wires	3/9/0	-
TC	A4.2.5	-	3	30	Bond Pull over Ball, post TC, 2X	Post stress	Wires	3/9/0	-
HTSL	A6.1	JEDEC JESD22- A103	3	45	High Temperature Storage Life	175C	500 Hours	3/135/0	-
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	3/3/0	-
HTSL	A6.2	JEDEC JESD22- A103	3	45	High Temperature Storage Life	175C	1000 Hours	3/132/0	-
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	3/3/0	-
Test Gro	oup B - A	Accelerated Lifetime Si	mulatior	Tests					
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	125C	1000 Hours	3/231/1 ¹	-
ELFR	B2	AEC Q100-008	1	77	Early Life Failure Rate	125C	48 Hours	3/2400/0	-
Test Gro	oup C - F	Package Assembly Inte	grity Tes	sts					
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	-
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	-
Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: BQ79616HPAPRQ1	QBS Reference: <u>BQ79616PAPRQ1</u>
SD	C3	JEDEC JESD22- B102	1	15	PB Solderability	>95% Lead Coverage	-	-	1/15/0
SD	C3	JEDEC JESD22- B102	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	1/15/0
PD	C4	JEDEC JESD22- B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	3/30/0	-
Test Gro	oup D - E	Die Fabrication Reliabili	ty Tests						
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Gro	oup E - E	Electrical Verification Te	sts						
	E2	AEC Q100-002	1	3	ESD HBM	-	2500 Volts	1/3/0	-
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	1000 Volts	1/3/0	-
LU	E4	AEC Q100-004	1	6	Latch-Up	Per AEC Q100-004	-	1/6/0	-
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	3/90/0	-

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

- QBS: Qual By Similarity
- Qual Device BQ79616HPAPRQ1 is qualified at MSL3 260C
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-NPD-2201-085

[1]-QEM-EVAL-2206-00212: EOS undetermined root cause. Contact QRE for 8D.

RFAB Qualification Plan

Qual Device	Req Name	Conditions	Lots	SS/Lot	Readpoints	Accept
BQ79616	Precon Q006 MSL3	MSL3 260C	3	0	1	1
BQ79616	Autoclave Q100	121C/15psig	3	77	96	96
BQ79616	BHAST Q006 (130C)	130C	3	77	96, 192	192
BQ79616	Ball Bond Pull Q006 1X	Post stress	3	3	1	1
BQ79616	Ball Bond Shear Q006 1X	Post stress	3	3	1	1
BQ79616	Stitch Bond Pull Q006 1X	Post stress	3	3	1	1
BQ79616	X-sec Q006 1x	Post stress cross section	3	1	1	1
BQ79616	SAM Q006	Review for delamination	3	22	1	1
BQ79616	Ball Bond Shear Q006 2X	Post stress	3	3	1	1
BQ79616	Ball Bond Shear Q006 2X	Post stress	3	3	1	1
BQ79616	Stitch Bond Pull Q006 2X	Post stress	3	3	1	1
BQ79616	X-sec Q006 2X	Post stress cross section	3	1	1	1
BQ79616	TC Q006 Grade 1 (-65C/+150C)	-65/150C	3	77	500, 1000, 1500	1000
BQ79616	SAM Q006	Review for delamination	3	22	1	1
BQ79616	Ball Bond Pull Q006 1X	Post stress	3	3	1	1
BQ79616	Ball Bond Shear Q006 1X	Post stress	3	3	1	1
BQ79616	Stitch Bond Pull Q006 1X	Post stress	3	3	1	1
BQ79616	X-sec Q006 1x	Post stress cross section	3	1	1	1
BQ79616	SAM Q006	Review for delamination	3	22	1	1
BQ79616	Ball Bond Pull Q006 2X	Post stress	3	3	1	1
BQ79616	Ball Bond Shear Q006 2X	Post stress	3	3	1	1
BQ79616	Stitch Bond Pull Q006 2X	Post stress	3	3	1	1

Qual Device	Req Name	Conditions	Lots	SS/Lot	Readpoints	Accept
BQ79616	X-sec Q006 2X	Post stress cross section	3	1	1	1
BQ79616	HTSL Q006 Grade 1 (150C)	150C	3	45	1000, 2000	2000
BQ79616	X-sec Q006 1x	Post stress cross section	3	1	1	1
BQ79616	X-sec Q006 2X	Post stress cross section	3	1	1	1
BQ79616	Characterization Q100	Cpk>1.67 Room, hot, and cold	3	30	1	1
BQ79616	Assembly MQ Q100	Per site specification	3	1	1	1
BQ79616	Ball Bond Pull Q100	Minimum of 5 devices, 30 wires Cpk>1.67	3	5	1	1
BQ79616	Ball Bond Shear Q100	Minimum of 5 devices, 30 wires Cpk>1.67	3	5	1	1
BQ79616	Stitch Bond Pull Q100	Minimum of 5 devices, 30 wires Cpk>1.67	3	5	1	1
BQ79616	Physical Dimensions Q100	Cpk>1.67	3	10	1	1
BQ79616	Solderability Pb Free Q100	Precondition w.155C Dry Bake (4 hrs +/- 15 minutes)	1	15	1	1
BQ79616	Solderability Pb Q100	Precondition w.155C Dry Bake (4 hrs +/- 15 minutes)	1	15	1	1

ZVEI ID: SEM-PW-13

For questions regarding this notice, e-mails can be sent to Change Management team or your local Field Sales Representative.

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale (www.ti.com/legal/termsofsale.html) or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.